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(54) **Title**: METHODS OF FORMING PATTERNS ON SUBSTRATES

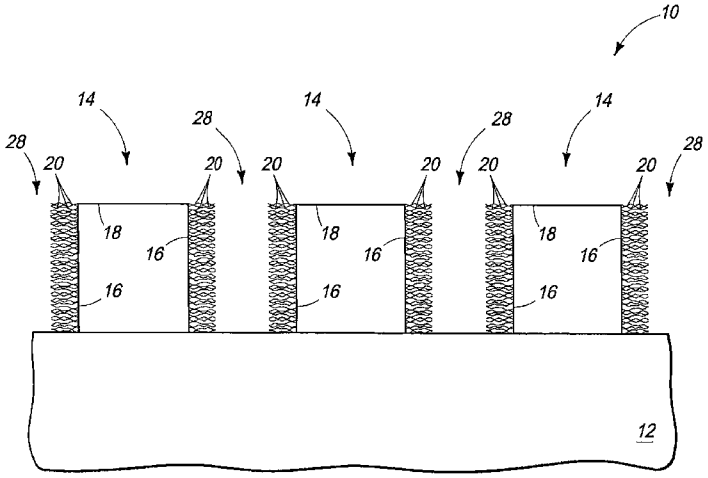


Fig. 4

(57) **Abstract**: A method of forming a pattern on a substrate includes forming spaced features over a substrate. A polymer is adsorbed to outer lateral surfaces of the spaced features. Either material of the spaced features is removed selectively relative to the adsorbed polymer or material of the adsorbed polymer is removed selectively relative to the spaced features to form a pattern on the substrate. In one embodiment, the polymer is of known chain length and has opposing longitudinal ends. One of the longitudinal ends of the polymer adsorbs to the outer lateral surfaces whereby the adsorbed polymer projects lengthwise from the outer lateral surfaces, with said chain length defining a substantially uniform lateral thickness of the adsorbed polymer on the spaced features. Additional embodiments are contemplated.

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